

Description

The WSD75N12GDN56 uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D
120V	6.0m Ω	75A

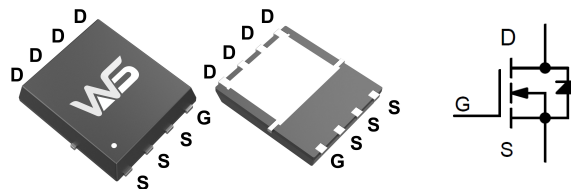
Application

- DC/DC Converter
- Load switch.

General Features

- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

DFN5X6-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	120	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹ ($T_c=25^\circ\text{C}$)	75	A
I_D	Continuous Drain Current ¹ ($T_c=70^\circ\text{C}$)	70	A
I_{DM}	Pulsed Drain Current	320	A
IAR	Single pulse avalanche current	40	A
E_{ASa}	Single pulse avalanche energy	240	mJ
P_D	Power Dissipation	125	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	120	--	--	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 120V, V _{GS} = 0V	--	--	1	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+20V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-20V	--	--	-100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250μA	2.5	3.0	3.5	V
R _{DS(ON)1}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =20A	--	6.0	6.8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =50A		130	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 50V f = 1.0MHz	--	4282	--	pF
C _{oss}	Output Capacitance		--	429	--	pF
C _{rss}	Reverse Transfer Capacitance		--	17	--	pF
R _g	Gate resistance		--	2.5	--	Ω
t _{d(ON)}	Turn-on Delay Time	I _D =20A V _{DS} = 50V V _{GS} = 10V R _G = 5Ω	--	20	--	ns
t _r	Rise Time		--	11	--	ns
t _{d(OFF)}	Turn-Off Delay Time		--	55	--	ns
t _f	Fall Time		--	28	--	ns
Q _g	Total Gate Charge	V _{GS} =0~10V V _{DS} = 50V I _D =20A	--	61.4	--	nC
Q _{gs}	Gate Source Charge		--	17.4	--	nC
Q _{gd}	Gate Drain Charge		--	14.1	--	nC
I _S	Diode Forward Current	T _C =25 °C	--	--	100	A
I _{SM}	Diode Pulse Current		--	--	320	A
V _{SD}	Diode Forward Voltage	I _S =6.0A, V _{GS} =0V	--	--	1.2	V
t _{rr}	Reverse Recovery time	I _S =20A, V _{DD} =50V dI _F /dt=100A/μs	--	100	--	ns
Q _{rr}	Reverse Recovery Charge		--	250	--	nC

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
- 3、 The EAS data shows Max. rating . The test condition is VDD=50V, L=0.3mH, Rg=25Ω, Starting T_J=25 °C
- 4、 The power dissipation is limited by 150°C junction temperature

Typical Electrical and Thermal Characteristics

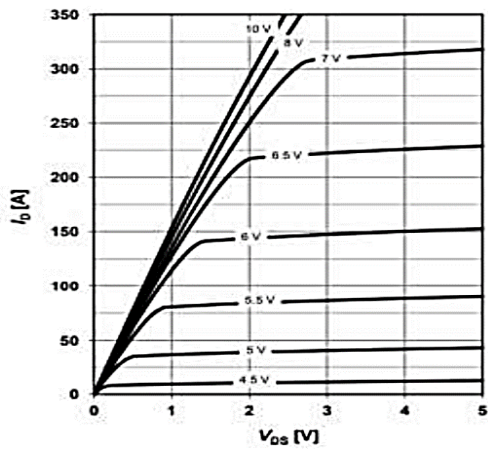


Figure1: output characteristics

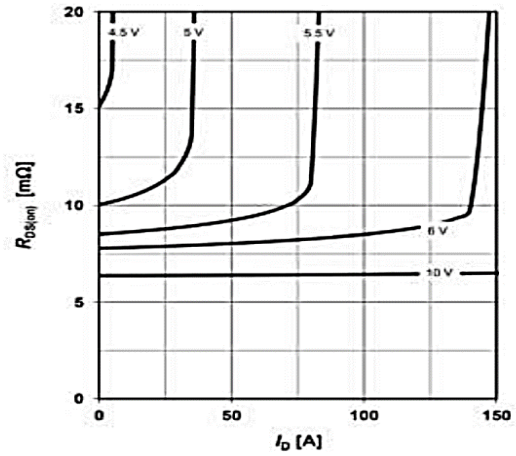


Figure2: Typical drain-source on resistance

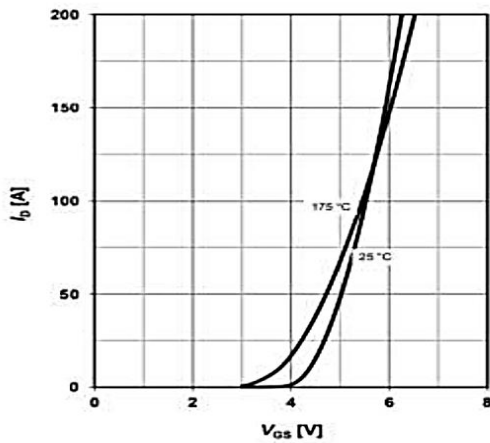


Figure3: transfer characteristics

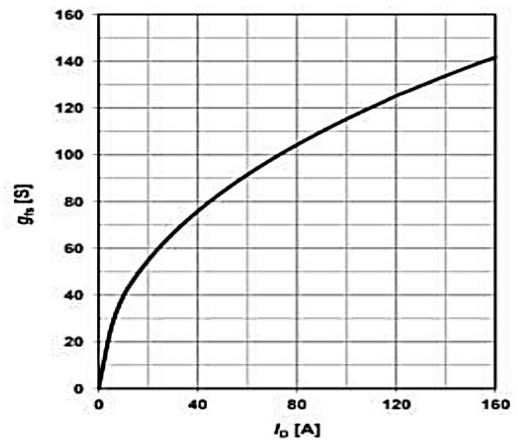


Figure4: forward transconductance

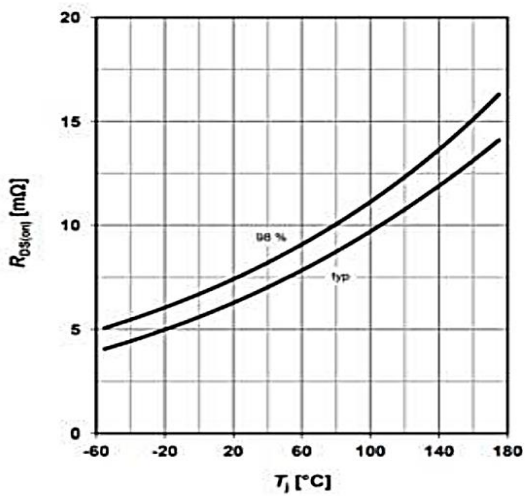


Figure5: Drain-source on-state resistance

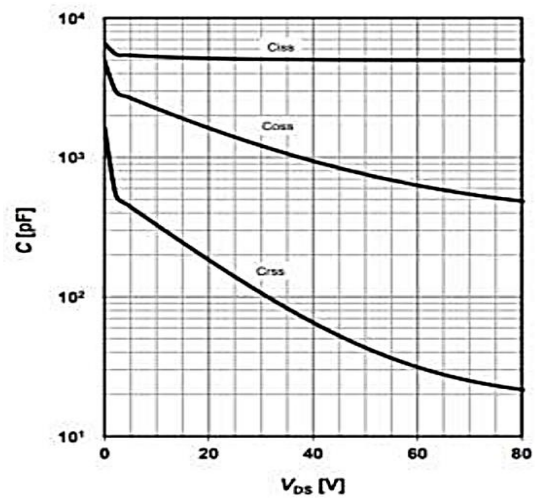


Figure6: Typ. capacitances

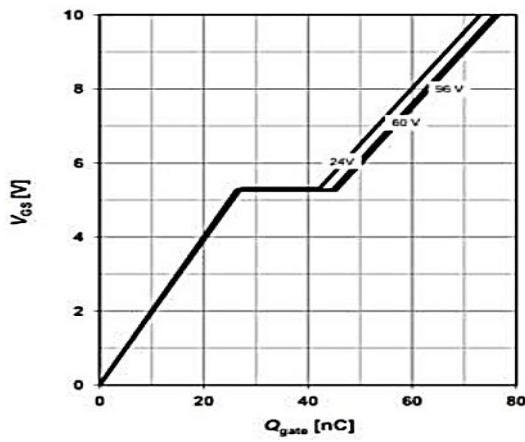


Figure7: Typ. gate charge

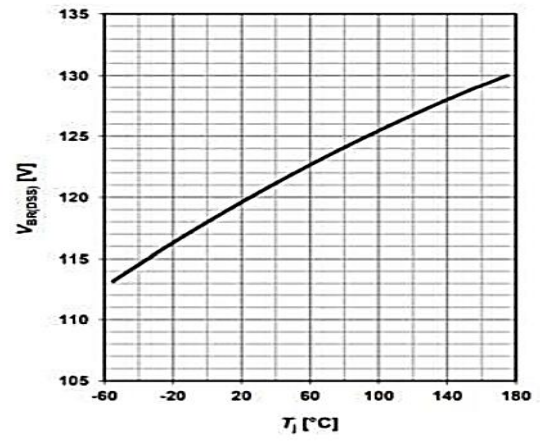


Figure8: Drain-source breakdown voltage

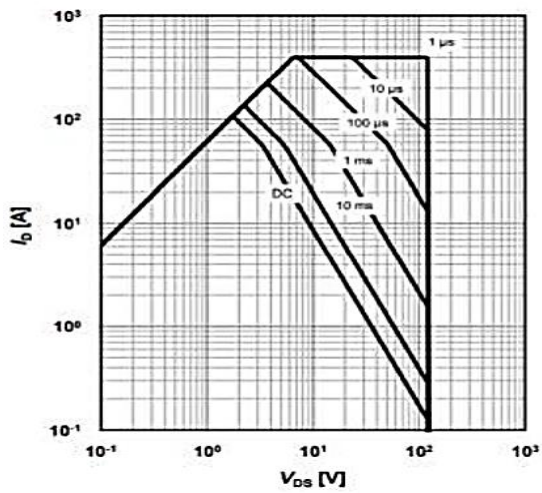


Figure9: Safe operating area

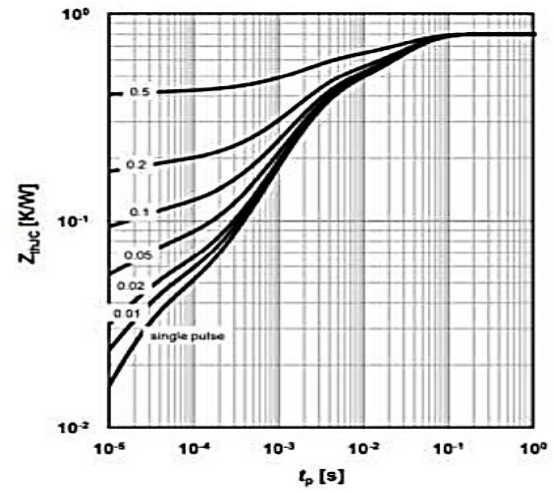


Figure10: Max. transient thermal impedance



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